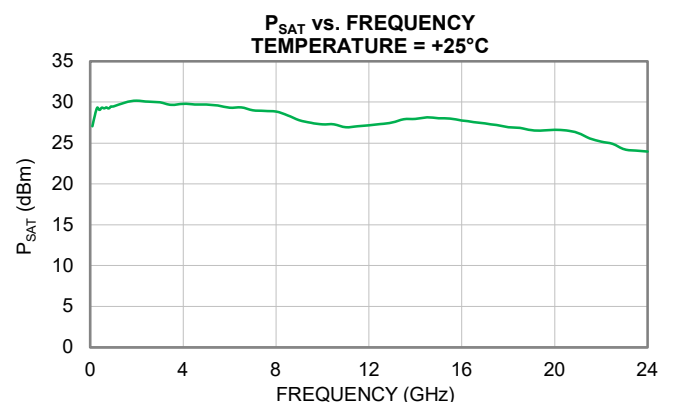
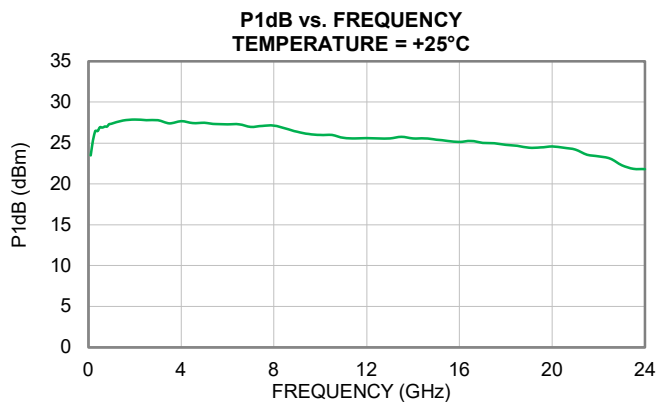
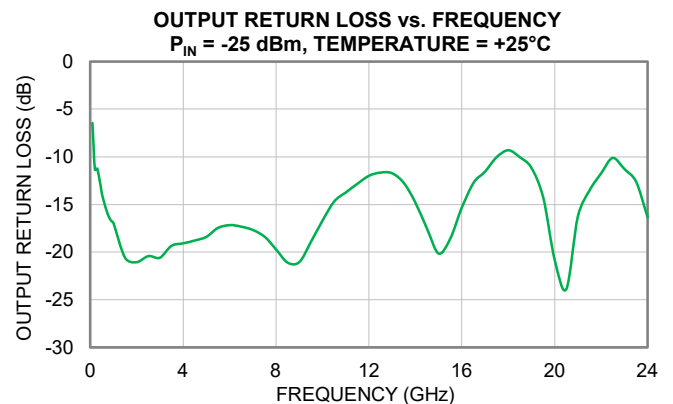
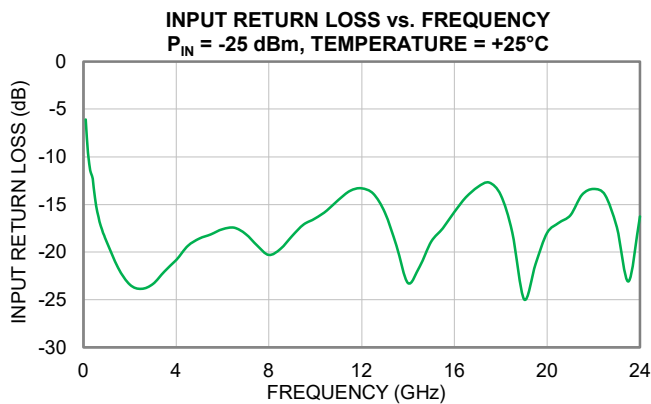
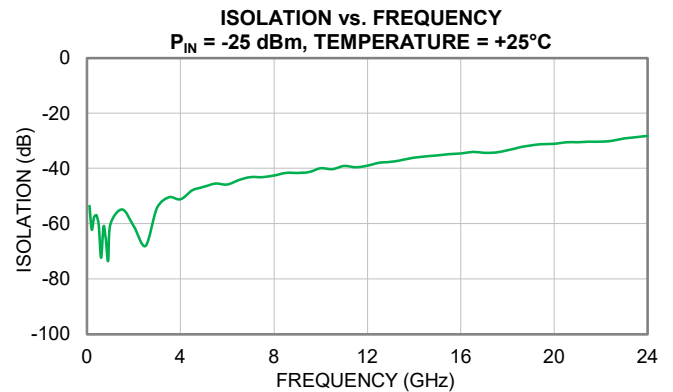
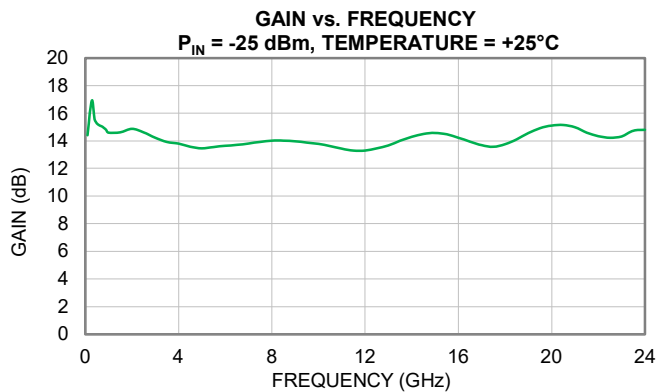


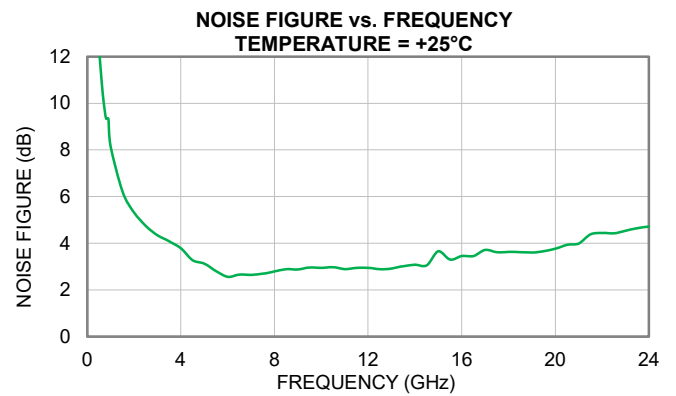
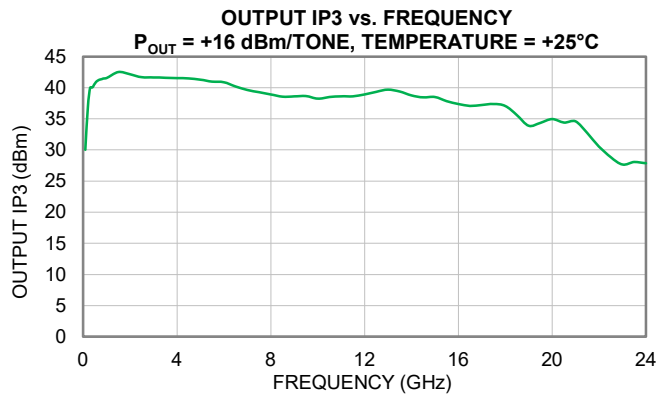
Typical Performance Curves

Note: Data was taken at $V_{DD} = +10$ V and $V_{GG2} = +3.5$ V. At $+25^{\circ}\text{C}$, V_{GG1} has been adjusted to achieve $I_{DD} = 300$ mA. For over voltage and temperature data, see AVA-223MP+.



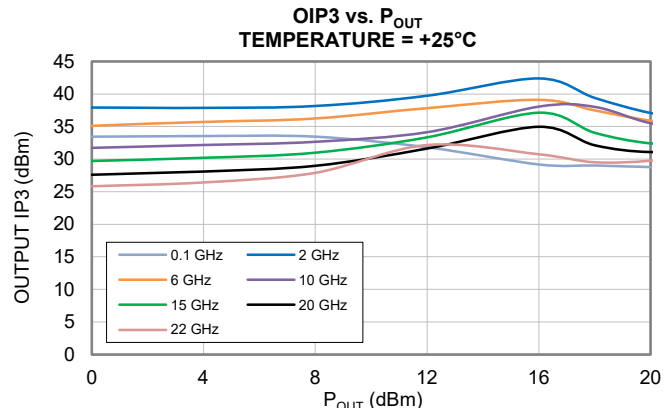
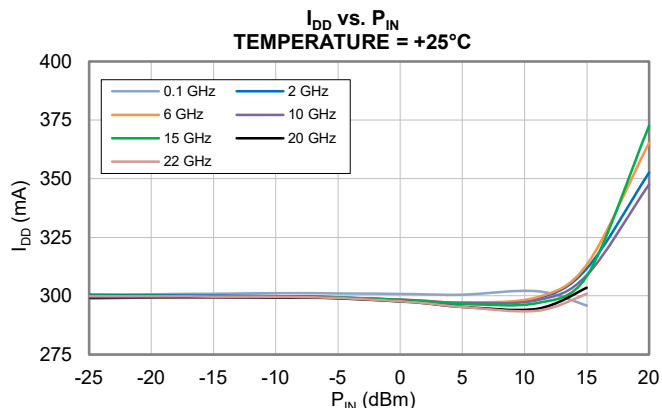
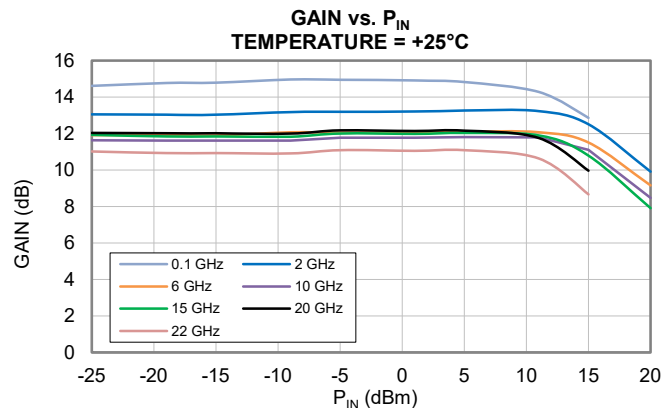
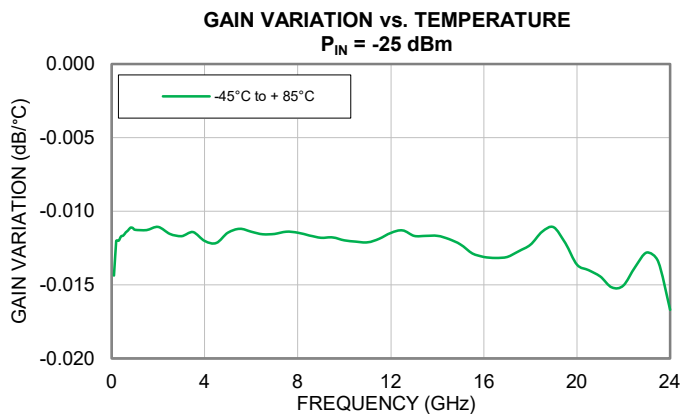
Typical Performance Curves

Note: Data was taken at $V_{DD} = +10$ V and $V_{GG2} = +3.5$ V. At $+25^{\circ}\text{C}$, V_{GG1} has been adjusted to achieve $I_{DD} = 300$ mA. For over voltage and temperature data, see AVA-223MP+.



Typical Performance Curves

Note: All data taken in this section represents the Die attached in a 5x5mm 32-Lead QFN-style package and measured on Mini-Circuits Characterization Test Board TB-AVA-223MPC+. Data was taken at $V_{DD} = +10$ V and $V_{GG2} = +3.5$ V. At $+25^{\circ}\text{C}$, V_{GG1} has been adjusted to achieve $I_{DD} = 300$ mA.



Typical Performance Curves

Note: All data taken in this section represents the die measured on modified Mini-Circuits Die Characterization Test Board using external bias tee (Figure 4). Data was taken at $V_{DD} = +10$ V and $V_{GG2} = +3.5$ V. At $+25^\circ\text{C}$, V_{GG1} has been adjusted to achieve $I_{DD} = 300$ mA.

